

April 1995

50A, 700V - 1000V Ultrafast Diodes

Features

- Ultrafast with Soft Recovery.....<125ns
- Operating Temperature.....+175°C
- Reverse Voltage Up To.....1000V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Description

RURU5070, RURU5080, RURU5090 and RURU50100 (TA9910) are ultrafast diodes with soft recovery characteristics ($t_{RR} < 125\text{ns}$). They have low forward voltage drop and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast recovery with soft recovery characteristic minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

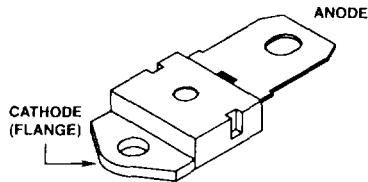
PACKAGING AVAILABILITY

PART NUMBER	PACKAGE	BRAND
RURU5070	TO-218	RURU5070
RURU5080	TO-218	RURU5080
RURU5090	TO-218	RURU5090
RURU50100	TO-218	RURU50100

NOTE: When ordering, use the entire part number.

Package

JEDEC STYLE SINGLE LEAD TO-218



Symbol



Absolute Maximum Ratings $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

	RURU5070	RURU5080	RURU5090	RURU50100	UNITS
Peak Repetitive Reverse Voltage.....	V_{RRM}	700	800	900	V
Working Peak Reverse Voltage	V_{PRM}	700	800	900	V
DC Blocking Voltage.....	V_R	700	800	900	V
Average Rectified Forward Current..... ($T_C = +88.6^\circ\text{C}$)	$I_{F(AV)}$	50	50	50	A
Repetitive Peak Surge Current..... (Square Wave, 20kHz)	I_{FSM}	100	100	100	A
Nonrepetitive Peak Surge Current..... (Halfwave, 1 Phase, 60Hz)	I_{FSM}	500	500	500	A
Maximum Power Dissipation	P_D	150	150	150	W
Avalanche Energy ($L = 40\text{mH}$).....	E_{AVL}	40	40	40	mj
Operating and Storage Temperature	T_{STG}, T_J	-65 to +175	-65 to +175	-65 to +175	$^\circ\text{C}$

Specifications RURU5070, RURU5080, RURU5090, RURU50100

Electrical Specifications $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	LIMITS												UNITS	
		RURU5070			RURU5080			RURU5090			RURU50100				
		MIN	Typ	MAX	MIN	Typ	MAX	MIN	Typ	MAX	MIN	Typ	MAX		
V_F	$I_F = 50\text{A}$	-	-	1.9	-	-	1.9	-	-	1.9	-	-	1.9	V	
V_F	$I_F = 50\text{A}, T_C = 150^\circ\text{C}$	-	-	1.7	-	-	1.7	-	-	1.7	-	-	1.7	V	
I_R	$V_R = 700\text{V}$	-	-	500	-	-	-	-	-	-	-	-	-	μA	
	$V_R = 800\text{V}$	-	-	-	-	-	500	-	-	-	-	-	-	μA	
	$V_R = 900\text{V}$	-	-	-	-	-	-	-	-	500	-	-	-	μA	
	$V_R = 1000\text{V}$	-	-	-	-	-	-	-	-	-	-	-	500	μA	
I_R	$V_R = 700\text{V}, T_C = 150^\circ\text{C}$	-	-	1.5	-	-	-	-	-	-	-	-	-	mA	
	$V_R = 800\text{V}, T_C = 150^\circ\text{C}$	-	-	-	-	-	1.5	-	-	-	-	-	-	mA	
	$V_R = 900\text{V}, T_C = 150^\circ\text{C}$	-	-	-	-	-	-	-	-	1.5	-	-	-	mA	
	$V_R = 1000\text{V}, T_C = 150^\circ\text{C}$	-	-	-	-	-	-	-	-	-	-	-	1.5	mA	
t_{RR}	$I_F = 1\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	125	-	-	125	-	-	125	-	-	125	ns	
	$I_F = 50\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	200	-	-	200	-	-	200	-	-	200	ns	
t_A	$I_F = 50\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	110	-	-	110	-	-	110	-	-	110	-	ns	
t_B	$I_F = 50\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	65	-	-	65	-	-	65	-	-	65	-	ns	
R_{BJC}		-	-	1.0	-	-	1.0	-	-	1.0	-	-	1.0	$^\circ\text{C}/\text{W}$	

DEFINITIONS

V_F = Instantaneous forward voltage ($pw = 300\mu\text{s}$, $D = 2\%$).

I_R = Instantaneous reverse current.

t_{RR} = Reverse recovery time (See Figure 2), summation of $t_A + t_B$.

t_A = Time to reach peak reverse current (See Figure 2).

t_B = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 2).

R_{BJC} = Thermal resistance junction to case.

E_{AVL} = Controlled avalanche energy (See Figures 7 and 8).

pw = pulse width.

D = duty cycle.

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ULTRAFAST
SINGLE DIODES

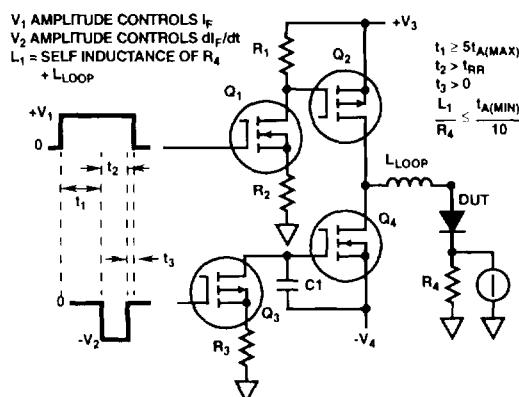


FIGURE 1. t_{RR} TEST CIRCUIT

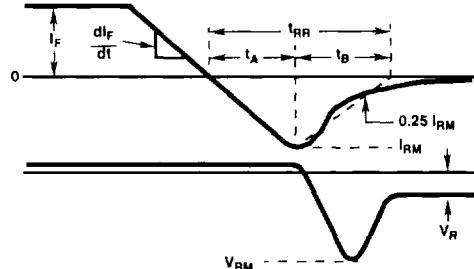


FIGURE 2. t_{RR} WAVEFORMS AND DEFINITIONS

Typical Performance Curves

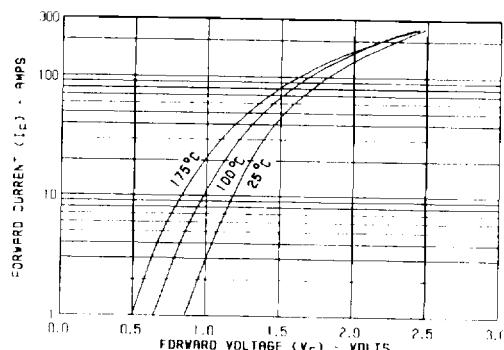


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

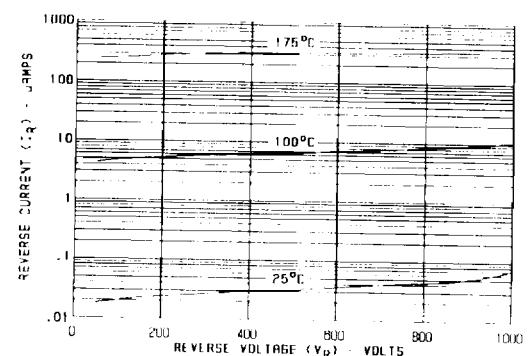


FIGURE 4. TYPICAL REVERSE CURRENT vs VOLTAGE

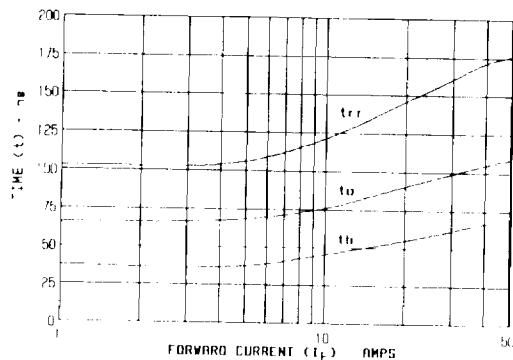


FIGURE 5. TYPICAL t_{rr} , t_A AND t_B CURVES vs FORWARD CURRENT

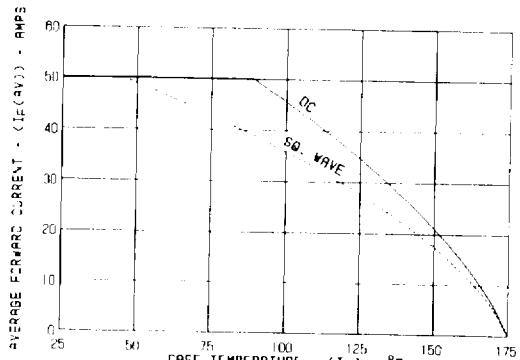


FIGURE 6. CURRENT DERATING CURVE FOR ALL TYPES

$$I_{MAX} = 1A$$

$$L = 40mH$$

$$R < 0.1\Omega$$

$$E_{AVL} = 1/2L^2 [V_{AVL}/(V_{AVL} - V_{DD})]$$

Q₁ & Q₂ ARE 1000V MOSFETs

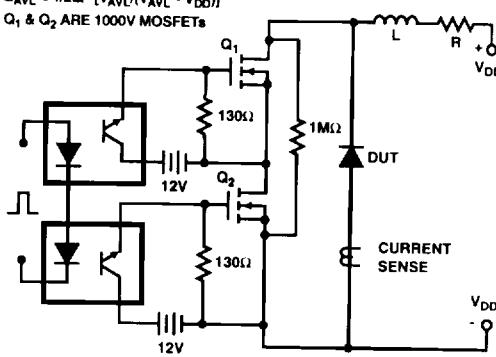


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

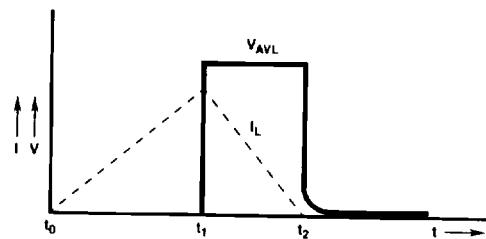


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS